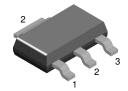


May 2009

NZT560/NZT560A NPN Low Saturation Transistor

Features

 These devices are designed with high current gain and low saturation voltage with collector currents up to 3A continuous.



1. Base 2. Collector 3. Emitter

Absolute Maximum Ratings* $T_A=25$ °C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{CEO}	Collector-Emitter Voltage	60	V	
V _{CBO}	Collector-Base Voltage 80			
V _{EBO}	Emitter-Base Voltage	5	V	
I _C	Collector Current - Continuous 3		А	
T _J , T _{STG}	Operating and Storage Junction Temperature Range - 55 to +150 °C		°C	

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics $T_A=25$ °C unless otherwise noted

Symbol	Davamatav	Ма	Linita	
	Parameter	NZT560	NZT560A	Units
P_{D}	Total Device Dissipation	1		W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125		°C/W

Symbol	Parameter Test Conditions		Min.	Max.	Units	
Off Chara	Off Characteristics					
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA	60		٧	
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 100\mu A$	80		V	
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100\mu A$	5		٧	
I _{CBO}	Collector Cutoff Current $V_{CB} = 30V$ $V_{CB} = 30V$, $T_{A} = 100$ °C			100 10	nΑ μΑ	
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V		100	nA	
On Chara	On Characteristics *					
h _{FE}	DC Current Gain	$\begin{tabular}{l l l l l l l l l l l l l l l l l l l $	70 100 250 80 25	300 550		
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_{C} = 1A, I_{B} = 100 \text{mA}$ $I_{C} = 3A, I_{B} = 300 \text{mA}$ NZT560 NZT560A		300 450 400	mV mV mV	
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 1A, I _B = 100mA		1.25	٧	
V _{BE} (on)	Base-Emitter On Voltage	I _C = 1A, V _{CE} = 2V		1	٧	
Small Sig	nal Characteristics					
C _{obo}	Output Capacitance	V _{CB} = 10V, I _E = 0, f = 1MHz		30	pF	
f _T	Transition Frequency	I _C = 100mA, V _{CE} = 5V, f = 100MHz	75		MHz	

^{*} Pulse Test: Pulse Width $\leq 300 \mu s, \ Duty \ Cycle \leq 2.0\%$

Typical Performance Characteristics

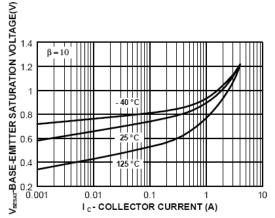


Figure 1. Base-Emitter Saturation Voltage vs Collector Current

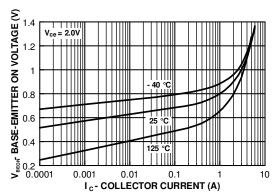


Figure 2. Base-Emitter On Voltage vs Collector Current

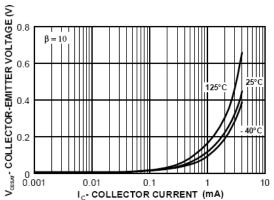


Figure 3. Collector-Emitter Saturation Voltage vs Collector Current

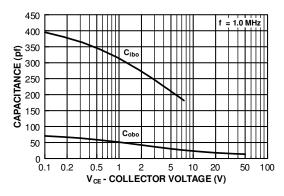


Figure 4. Input/Output Capacitance vs Reverse Bias Voltage

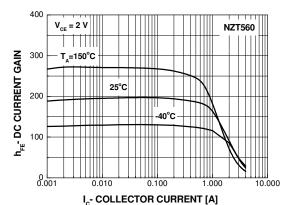


Figure 5. Current Gain vs Collector Current

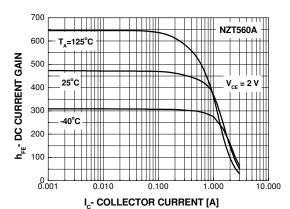
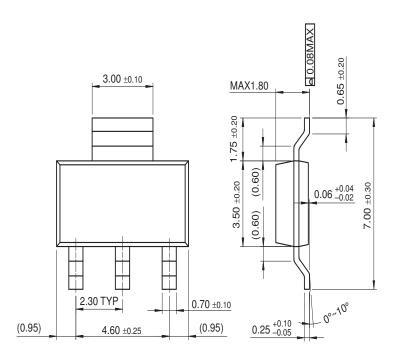
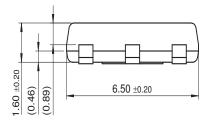


Figure 6. Current Gain vs Collector Current

Physical Dimensions

SOT-223





Dimensions in Millimeters





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Definition of Terms			
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